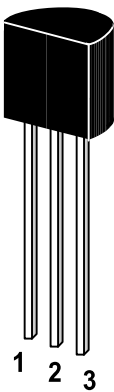


ST 2SA1270

PNP Silicon Epitaxial Planar Transistor
for switching and general purpose applications.

The transistor is subdivided into two groups O and Y
according to its DC current gain.

On special request, these transistors can be
manufactured in different pin configurations.



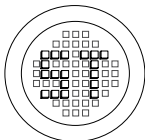
1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a=25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	35	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	30	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	500	mA
Base Current	$-I_{\text{B}}$	100	mA
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_{j}	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{s}	-55 to +150	$^{\circ}\text{C}$

G S P FORM A IS AVAILABLE



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РАДИОТЕХ-ТРЕЙД

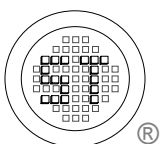
Тел.: (495) 795-0805
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Эл. почта: info@rct.ru
Веб: www.rct.ru

ST 2SA1270

Characteristics at $T_{amb}=25^{\circ}C$

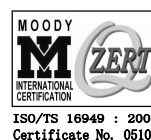
	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE}=1V, -I_C=100mA$					
Current Gain Group O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
at $-V_{CE}=6V, -I_C=400mA$					
O	h_{FE}	25	-	-	-
Y	h_{FE}	40	-	-	-
Collector Cutoff Current					
at $-V_{CB}=35V$	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current					
at $-V_{EB}=5V$	$-I_{EBO}$	-	-	0.1	μA
Collector Emitter Saturation Voltage					
at $-I_C=100mA, -I_B=10mA$	$-V_{CEsat}$	-	0.1	0.25	V
Base Emitter Voltage					
at $-V_{CE}=1V, -I_C=100mA$	$-V_{BE}$	-	0.8	1.0	V
Transition Frequency					
at $-V_{CE}=6V, -I_C=20mA$	f_T	-	200	-	MHz
Collector Output Capacitance					
at $-V_{CB}=6V, f=1MHz$	C_{OB}	-	13	-	pF

G S P FORM A IS AVAILABLE



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, acompany
listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 07/12/2002